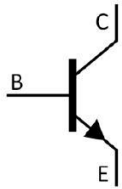


Silicon NPN transistor in a TO-220F Plastic Package.

High f_T , complementary pair with .

General power and driver stage amplifier applications.

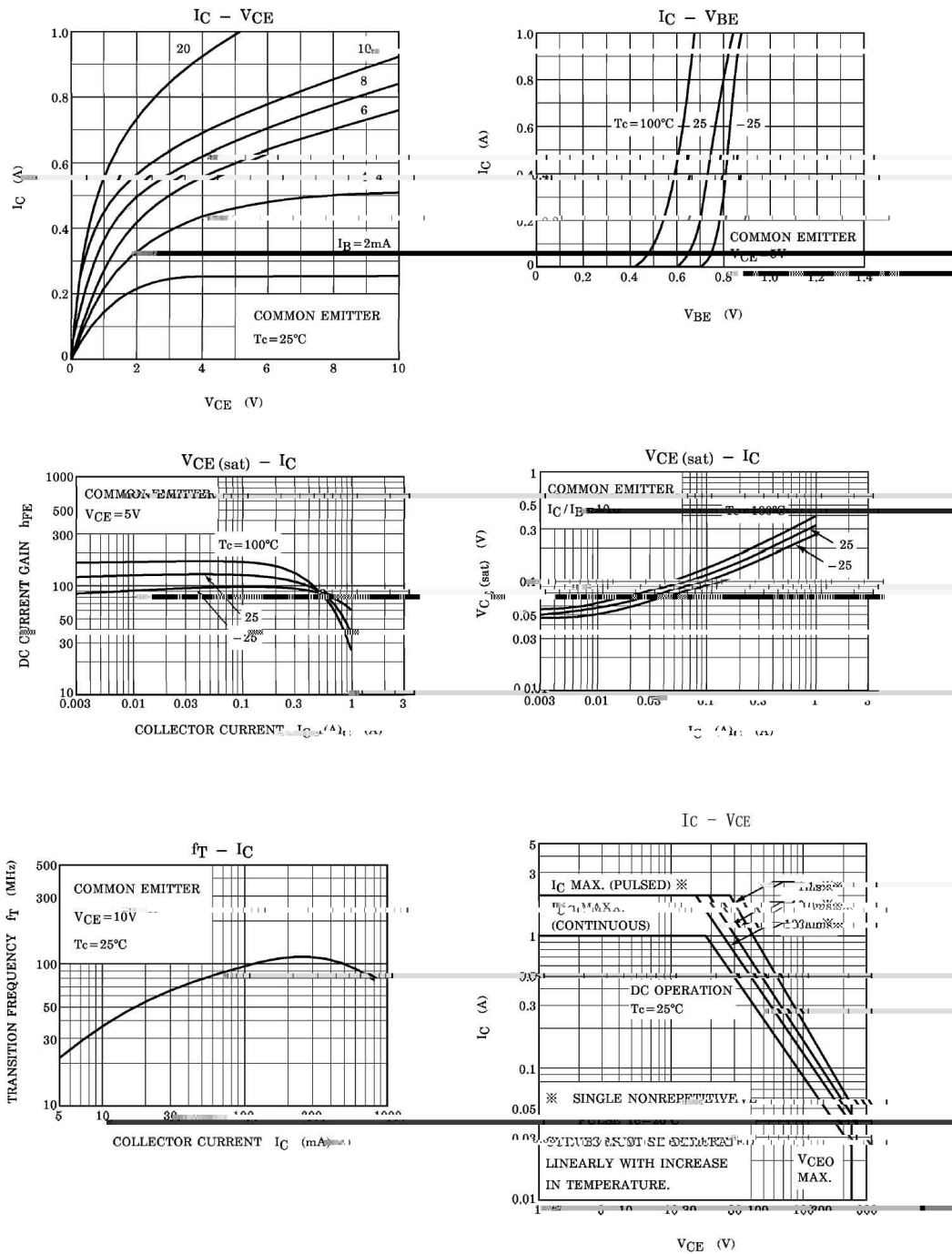


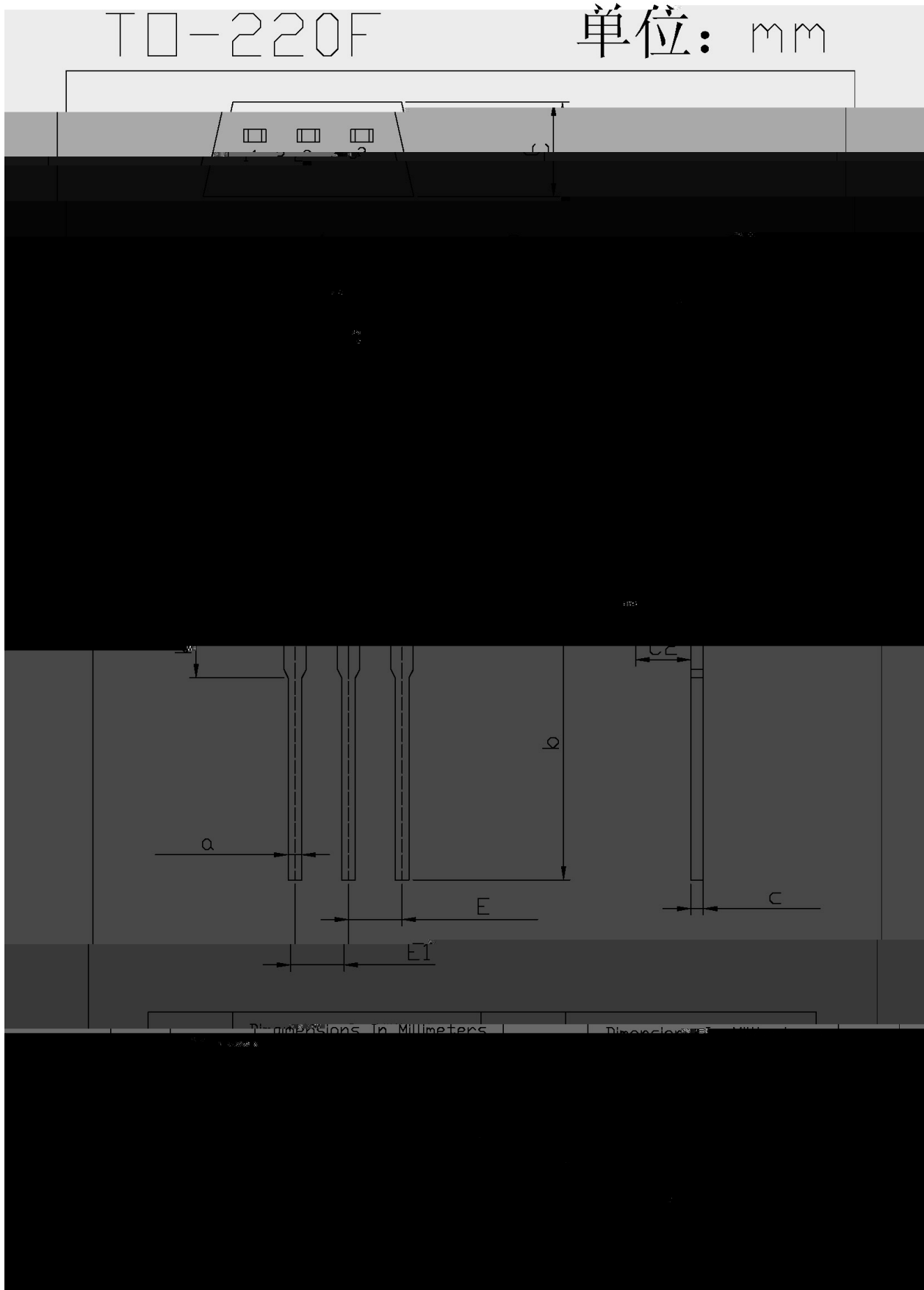
PIN1 Base PIN 2 Collector PIN 3 Emitter

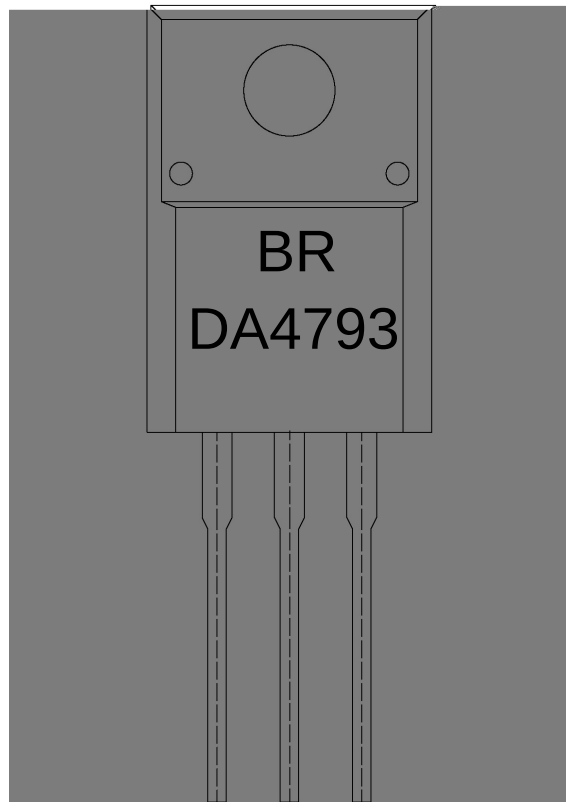
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	230	V
Collector to Emitter Voltage	V_{CEO}	230	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.0	A
Base Current - Continuous	I_B	0.1	A
Collector Power Dissipation	P_C	2.0	W
	$P_{C(T_c=25^\circ C)}$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	230			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=230V$ $I_E=0$			1.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=100mA$	100		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA$ $I_B=50mA$			1.5	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=5.0V$ $I_C=500mA$			1.0	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=100mA$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		20		pF







BR

Note:

BR: Company Code.

DA4793: Product Type.

***: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

270 5

10 1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱